

Jinn-Kong Sheu

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Sea-Urchin-Like Bi ₂ S ₃ Microstructures Decorated with Graphitic Carbon Nitride Nanosheets for Use in Food Preservation. ACS Applied Nano Materials, 2022, 5, 2375-2384.	5.0	31
2	High-Responsivity Solar-Blind Photodetectors Formed by Ga ₂ O ₃ /p-GaN Bipolar Heterojunctions. ACS Photonics, 2022, 9, 1002-1007.	6.6	18
3	Improved Performance of GaN Photoelectrodes from the Facile Fabrication of a Binder-Free Catalyst: Ni(OH) ₂ Nanosheets. ACS Applied Energy Materials, 2022, 5, 3471-3476.	5.1	2
4	AlGa _x N-Based Deep Ultraviolet Light-Emitting Diodes with Thermally Oxidized Al _x Ga _{2-2x} O ₃ Sidewalls. ACS Omega, 2022, 7, 15027-15036.	3.5	4
5	InGa _x N-based light-emitting diodes with Al content graded p-Al _x Ga _{1-x} N top contact layer. Physica E: Low-Dimensional Systems and Nanostructures, 2022, 143, 115352.	2.7	1
6	Effects of Thermal Annealing on the Properties of Zirconium-Doped Mg _x Zn _{1-x} O Films Obtained through Radio-Frequency Magnetron Sputtering. Membranes, 2021, 11, 373.	3.0	4
7	Stable Photoelectrochemical Water Splitting Using n GaN Junction Decorated with Nickel Oxides as Photoanodes. Journal of Physical Chemistry C, 2021, 125, 16776-16783.	3.1	10
8	Effect of KOH-Treatment at Sol-Gel Derived NiO _x Film on GaN Photoanodes in Hydrogen Generation. ACS Applied Energy Materials, 2021, 4, 8030-8035.	5.1	0
9	Achievement of 110-nm-Wide Spectral Width in Monolithic Tunnel-Junction Light-Emitting Diode. IEEE Journal of Quantum Electronics, 2021, 57, 1-6.	1.9	0
10	Scalable and sustainable synthetic assessment between solid-state metathesis and sonochemically derived electrocatalysts (strontium molybdate) for the precise anti-androgen bicalutamide (Casodex [®]) detection. Microchemical Journal, 2021, 168, 106465.	4.5	7
11	Deep Ultraviolet AlGa _x N-Based Light-Emitting Diodes with p-AlGa _x N/AlGa _x N Superlattice Hole Injection Structures. Processes, 2021, 9, 1727.	2.8	3
12	Terahertz Photoacoustic Generation Using Ultrathin Nickel Nanofilms. Journal of Physical Chemistry C, 2021, 125, 3134-3142.	3.1	9
13	Hydrothermal-Dependent Synthesis of Exfoliated Nickel Cobaltite Layers for Simultaneous Determination of IARC Group 2B, 3B Carcinogens. ACS Applied Nano Materials, 2021, 4, 12788-12797.	5.0	10
14	Suppressing the Initial Growth of Sidewall GaN by Modifying AlN-Coated Patterned Sapphire with KOH-Based Etchant. ECS Journal of Solid State Science and Technology, 2020, 9, 016012.	1.8	0
15	Studying time-dependent contribution of hot-electron versus lattice-induced thermal-expansion response in ultra-thin Au-nanofilms. Applied Physics Letters, 2020, 117, .	3.3	5
16	Al _{0.3} Ga _{0.7} N/GaN heterostructure transistors with a regrown p-GaN gate formed with selective-area Si implantation as the regrowth mask. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 124, 114367.	2.7	3
17	Rationally designed RGO@CuO@Mn ₂ O ₃ as an excellent electrocatalyst for the rapid and real-time detection of 2-nitrophenol. New Journal of Chemistry, 2020, 44, 12465-12472.	2.8	24
18	Cobalt Oxide Nanofilms on n-GaN Working Electrodes for Photoelectrochemical Water Splitting. Journal of Physical Chemistry C, 2020, 124, 25196-25201.	3.1	2

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19	NiOx nanoparticles as active water splitting catalysts for the improved photostability of a n-GaN photoanode. <i>Solar Energy Materials and Solar Cells</i> , 2020, 216, 110723.	6.2	6
20	Observation of Femtosecond Acoustic Anomaly in a Solid Liquid Interface. <i>Journal of Physical Chemistry C</i> , 2020, 124, 2987-2993.	3.1	4
21	Photoelectrochemical Generation of Hydrogen and Formic Acid Using GaN Films Decorated with TiO ₂ /Ag Nanoparticles Composite Structure as Photoelectrodes. <i>Journal of Physical Chemistry C</i> , 2020, 124, 9591-9598.	3.1	10
22	AlGaIn-based deep ultraviolet light emitting diodes with magnesium delta-doped AlGaIn last barrier. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	17
23	High-power and single-mode VCSEL arrays with single-polarized outputs by using package-induced tensile strain. <i>Optics Letters</i> , 2020, 45, 4839.	3.3	14
24	UV light-emitting diodes grown on GaN templates with selective-area Si implantation. <i>Optics Express</i> , 2020, 28, 4674.	3.4	4
25	Ultra-short photoacoustic pulse generation through hot electron pressure in two-dimensional electron gas. <i>Optics Express</i> , 2020, 28, 34045.	3.4	0
26	Enhanced production rates of hydrogen generation and carbon dioxide reduction using aluminum gallium nitride/gallium nitride heteroepitaxial films as photoelectrodes in seawater. <i>Solar Energy Materials and Solar Cells</i> , 2019, 202, 110153.	6.2	8
27	Graphene Quantum Dot Vertical Cavity Surface-Emitting Lasers. <i>ACS Photonics</i> , 2019, 6, 2894-2901.	6.6	8
28	A curvature-tunable random laser. <i>Nanoscale</i> , 2019, 11, 3534-3545.	5.6	50
29	Investigation on Modulation Speed of Photon-Recycling White Light-Emitting Diodes With Vertical-Conduction Structure. <i>Journal of Lightwave Technology</i> , 2019, 37, 1225-1230.	4.6	2
30	Verification of complex acoustic mismatch model in sub-THz regime. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	9
31	Light-emitting diodes with surface gallium nitride μ n homojunction structure formed by selective area regrowth. <i>Scientific Reports</i> , 2019, 9, 3243.	3.3	21
32	A random laser with tunable threshold by bending curvature. , 2019, , .		0
33	Mn valence state mediated room temperature ferromagnetism in nonpolar Mn doped GaN. <i>Applied Surface Science</i> , 2019, 473, 693-698.	6.1	20
34	Bending-induced tunable threshold in random laser. , 2019, , .		0
35	Design of GaN-Based Multicolor Tunnel-Junction Light-Emitting Diodes. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 165-171.	3.0	5
36	Suppressing the Initial Growth of Sidewall GaN by Modifying Micron-Sized Patterned Sapphire Substrate with H ₃ PO ₄ -Based Etchant. <i>Micromachines</i> , 2018, 9, 622.	2.9	3

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37	GaN intermediate band solar cells with Mn-doped absorption layer. Scientific Reports, 2018, 8, 8641.	3.3	11
38	GaN-Based Cyan Light-Emitting Diode with up to 1-GHz Bandwidth for High-Speed Transmission Over SI-POF. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	11
39	InGaN-based epitaxial films as photoelectrodes for hydrogen generation through water photoelectrolysis and CO2 reduction to formic acid. Solar Energy Materials and Solar Cells, 2017, 166, 86-90.	6.2	32
40	Photoelectrochemical hydrogen generation from water using undoped GaN with selective-area Si-implanted stripes as a photoelectrode. Journal of Materials Chemistry A, 2017, 5, 22625-22630.	10.3	7
41	In Situ Monitoring of Chemical Reactions at a Solid-Water Interface by Femtosecond Acoustics. Journal of Physical Chemistry Letters, 2017, 8, 5430-5437.	4.6	12
42	Carrier dynamics of Mn-induced states in GaN thin films. Scientific Reports, 2017, 7, 5788.	3.3	8
43	Theoretical Investigation of Efficient Green Tunnel-Junction Light-Emitting Diodes. IEEE Electron Device Letters, 2017, 38, 75-78.	3.9	6
44	Extracting elastic properties of an atomically thin interfacial layer by time-domain analysis of femtosecond acoustics. Applied Physics Letters, 2017, 111, 213101.	3.3	6
45	Planar GaN-Based Blue Light-Emitting Diodes With Surface p-n Junction Formed by Selective-Area Ion Implantation. IEEE Transactions on Electron Devices, 2017, 64, 4156-4160.	3.0	11
46	The development of high-speed III-nitride based light-emitting diode for visible light and plastic optical fiber communications. , 2017, , .		0
47	Monolithic stacked blue light-emitting diodes with polarization-enhanced tunnel junctions. Optics Express, 2017, 25, A777.	3.4	6
48	III-V Nitride-Based Photodetection. Series in Optics and Optoelectronics, 2017, , 597-613.	0.0	0
49	GaN based Cyan light-emitting diodes with GHz bandwidth. , 2016, , .		4
50	Manganese-doped AlGaIn/GaN heterojunction solar cells with intermediate band absorption. Solar Energy Materials and Solar Cells, 2016, 157, 727-732.	6.2	16
51	Multiple-layered type-II GaSb/GaAs quantum ring solar cells under concentrated solar illumination. , 2016, , .		0
52	THz Acoustic Spectroscopy by using Double Quantum Wells and Ultrafast Optical Spectroscopy. Scientific Reports, 2016, 6, 28577.	3.3	7
53	Physical properties of Al-doped MgZnO/AlGaIn heterojunction photodetectors. Optical and Quantum Electronics, 2016, 48, 1.	3.3	2
54	III-Nitride Based Cyan Light-Emitting Diodes with GHz Bandwidth for High-Speed Visible Light Communication. IEEE Electron Device Letters, 2016, , 1-1.	3.9	30

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55	Enhancing UV-emissions through optical and electronic dual-function tuning of Ag nanoparticles hybridized with n-ZnO nanorods/p-GaN heterojunction light-emitting diodes. <i>Nanoscale</i> , 2016, 8, 4463-4474.	5.6	27
56	GaN-Based UV Light-Emitting Diodes With a Green Indicator Through Selective-Area Photon Recycling. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 1122-1127.	3.0	2
57	Mask-free regrowth of GaN p-i-n structure on selective-area Si-implanted n-GaN template layer. <i>Acta Materialia</i> , 2016, 108, 17-25.	7.9	5
58	Design of Hole-Blocking and Electron-Blocking Layers in Al _x Ga _{1-x} N-Based UV Light-Emitting Diodes. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 1141-1147.	3.0	32
59	Characterization of Nb-doped MgZnO films grown by a radio-frequency magnetron sputtering system. , 2015, , .		0
60	Positioning effect of type-II GaSb/GaAs quantum ring layer on solar cell performances. , 2015, , .		2
61	Al-doped MgZnO/p-AlGaIn heterojunction and their application in ultraviolet photodetectors. <i>Proceedings of SPIE</i> , 2015, , .	0.8	0
62	Warm-white light-emitting diode with high color rendering index fabricated by combining trichromatic InGaIn emitter with single red phosphor. <i>Optics Express</i> , 2015, 23, A232.	3.4	16
63	GaN-based photon-recycling green light-emitting diodes with vertical-conduction structure. <i>Optics Express</i> , 2015, 23, A371.	3.4	5
64	White emission from non-planar InGaIn/GaN MQW LEDs grown on GaN template with truncated hexagonal pyramids. <i>Optics Express</i> , 2015, 23, A401.	3.4	23
65	Effects of Temperature on Niobium-Doped MgZnO Films Grown Using Radio-Frequency Magnetron Sputtering. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, Q96-Q100.	1.8	1
66	Vertical GaN-Based LEDs With Naturally Textured Surface Formed by Patterned Sapphire Substrate With Self-Assembled Ag Nanodots as Etching Mask. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 2919-2923.	3.0	5
67	THz acoustic phonon spectroscopy and nanoscopy by using piezoelectric semiconductor heterostructures. <i>Ultrasonics</i> , 2015, 56, 52-65.	3.9	44
68	Determination of s-d exchange coupling in GaMnN by time-resolved Kerr rotation spectroscopy. <i>Physical Review B</i> , 2014, 90, .	3.2	3
69	Photoelectrochemical hydrogen generation with linear gradient Al composition dodecagon faceted AlGaIn/n-GaN electrode. <i>Optics Express</i> , 2014, 22, A1853.	3.4	4
70	Slanted n-ZnO/p-GaN nanorod arrays light-emitting diodes grown by oblique-angle deposition. <i>APL Materials</i> , 2014, 2, 056101.	5.1	27
71	THz acoustic spectroscopy based on GaN nanostructures. <i>Proceedings of SPIE</i> , 2014, , .	0.8	0
72	Vertical InGaIn-based green-band solar cells operating under high solar concentration up to 300 suns. <i>Optics Express</i> , 2014, 22, A1222.	3.4	20

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73	Improved light extraction of nitride-based flip-chip light-emitting diodes by forming air voids on Ar-implanted sapphire substrate. , 2014, , .		0
74	Thermal stability of post-growth-annealed Ga-doped MgZnO films grown by the RF sputtering method. Materials Research Society Symposia Proceedings, 2014, 1675, 41-44.	0.1	0
75	Temperature-Dependent Current-Voltage Characteristics of Al-Doped Mg _x Zn _{1-x} O/AlGaIn _n -i-p Junction Diodes. ECS Journal of Solid State Science and Technology, 2014, 3, Q65-Q68.	1.8	8
76	Surface Plasmon-Enhanced GaN Metal-Insulator-Semiconductor Ultraviolet Detectors With Ag Nanoislands Embedded in a Silicon Dioxide Gate Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 137-141.	2.9	7
77	Selective Growth of AlGaIn-Based p-i-n UV Photodiodes Structures. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 173-177.	2.9	3
78	Ultraviolet/blue light-emitting diodes based on single horizontal ZnO microrod/GaN heterojunction. Nanoscale Research Letters, 2014, 9, 446.	5.7	20
79	Ga ₂ O ₃ Films for Photoelectrochemical Hydrogen Generation. Journal of the Electrochemical Society, 2014, 161, H508-H511.	2.9	23
80	Passively gain-switched and self mode-locked thulium fiber laser at 1950nm. Optics and Laser Technology, 2014, 56, 354-357.	4.6	19
81	Probing Hydrophilic Interface of Solid/Liquid-Water by Nanoultrasonics. Scientific Reports, 2014, 4, 6249.	3.3	45
82	GaN-Based Dual-Color LEDs With λ -Type Insertion Layer for Controlling the Ratio of Two-Color Intensities. IEEE Transactions on Electron Devices, 2013, 60, 2821-2826.	3.0	6
83	Efficiency enhancement of InGaIn/GaN multiple quantum well solar cells using CdS quantum dots and distributed Bragg reflectors. , 2013, , .		1
84	Improving efficiency of InGaIn/GaN multiple quantum well solar cells using CdS quantum dots and distributed Bragg reflectors. Solar Energy Materials and Solar Cells, 2013, 117, 531-536.	6.2	31
85	Efficient collection of photogenerated carriers by inserting double tunnel junctions in III-nitride p-i-n solar cells. Applied Physics Letters, 2013, 103, 193503.	3.3	9
86	Improved Output Power of GaN-based Blue LEDs by Forming Air Voids on Ar-Implanted Sapphire Substrate. Journal of Lightwave Technology, 2013, 31, 1318-1322.	4.6	16
87	GaN-Based Planar p-i-n Photodetectors With the Be-Implanted Isolation Ring. IEEE Transactions on Electron Devices, 2013, 60, 1178-1182.	3.0	14
88	Photoresponses of manganese-doped gallium nitride grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2013, 102, .	3.3	9
89	Enhanced AlGaIn/GaN MOS-HEMT Performance by Using Hydrogen Peroxide Oxidation Technique. IEEE Transactions on Electron Devices, 2013, 60, 213-220.	3.0	62
90	Dual-wavelength GaN-based LEDs grown on truncated hexagonal pyramids formed by selective-area regrowth on Si-implanted GaN templates. Optics Express, 2013, 21, A864.	3.4	8

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91	THz Acoustic Attenuation of Silica studied by Ultrafast Acoustic Phonon Spectroscopy. , 2013, , .		0
92	Current-voltage characteristics of n-AlMgZnO/p-GaN junction diodes. , 2013, , .		0
93	Numerical study of the suppressed efficiency droop in blue InGaN LEDs with polarization-matched configuration. Optics Letters, 2013, 38, 3158.	3.3	10
94	InGaN working electrodes with assisted bias generated from GaAs solar cells for efficient water splitting. Optics Express, 2013, 21, A991.	3.4	12
95	Acoustic spectroscopy for studies of vitreous silica up to 740 GHz. AIP Advances, 2013, 3, 072126.	1.3	7
96	Improved conversion efficiency of GaN-based solar cells with Mn-doped absorption layer. Applied Physics Letters, 2013, 103, 063906.	3.3	19
97	Thermal Boundary Resistance between GaN and Cubic Ice and THz Acoustic Attenuation Spectrum of Cubic Ice from Complex Acoustic Impedance Measurements. Physical Review Letters, 2013, 111, 225901.	7.8	17
98	InGaN Flip-Chip Light-Emitting Diodes With Embedded Air Voids as Light-Scattering Layer. IEEE Electron Device Letters, 2013, 34, 1542-1544.	3.9	8
99	GaN-Based Dual Color LEDs with P-Type Insertion Layer for Balancing Two-Color Intensities. , 2013, , .		1
100	High-temperature stability of postgrowth-annealed Al-doped Mg _x Zn _{1-x} O films without the phase separation effect. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	1.2	5
101	Modulation Effects of Periodic Potentials on the Electronic Properties of Bilayer Bernal Graphene: Tight-Binding Model. Journal of the Physical Society of Japan, 2012, 81, 014705.	1.6	2
102	Vertical InGaN light-emitting diodes with a sapphire-face-up structure. Optics Express, 2012, 20, A119.	3.4	11
103	Immersed finger-type indium tin oxide ohmic contacts on p-GaN photoelectrodes for photoelectrochemical hydrogen generation. Optics Express, 2012, 20, A190.	3.4	10
104	Femtosecond excitation of radial breathing mode in 2-D arrayed GaN nanorods. Optics Express, 2012, 20, 16611.	3.4	13
105	Sputtered ZnO/SiO ₂ nanocomposite light-emitting diodes with flat-top nanosecond laser treatment. Optics Express, 2012, 20, 19635.	3.4	5
106	Vertical InGaN light-emitting diode with a retained patterned sapphire layer. Optics Express, 2012, 20, A1019.	3.4	7
107	Optical properties of Mn in regrown GaN-based epitaxial layers. Optical Materials Express, 2012, 2, 469.	3.0	5
108	Mn-doped GaN as photoelectrodes for the photoelectrolysis of water under visible light. Optics Express, 2012, 20, A678.	3.4	14

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109	GaN-Based Miniaturized Cyan Light-Emitting Diodes on a Patterned Sapphire Substrate With Improved Fiber Coupling for Very High-Speed Plastic Optical Fiber Communication. IEEE Photonics Journal, 2012, 4, 1520-1529.	2.0	42
110	GaN-based light emitting diodes with micro- and nano-patterned structures by femtosecond laser nonlinear decomposition. Applied Physics Letters, 2012, 101, 131103.	3.3	13
111	Carrier Dynamics in High-Efficiency Blue GaN Light-Emitting Diodes Under Different Bias Currents and Temperatures. IEEE Photonics Journal, 2012, 4, 1870-1880.	2.0	2
112	Confined acoustic vibrations in piezoelectric GaN nanorods. , 2012, , .		2
113	Improved Output Power of InGaN LEDs by Lateral Overgrowth on Si-Implanted n-GaN Surface to Form Air Gaps. IEEE Journal of Quantum Electronics, 2012, 48, 1004-1009.	1.9	6
114	Light Extraction Enhancement of GaN-Based Light-Emitting Diodes Using Crown-Shaped Patterned Sapphire Substrates. IEEE Photonics Technology Letters, 2012, 24, 1212-1214.	2.5	8
115	Non-alloyed Cr/Au Ohmic contacts to N-face and Ga-face n-GaN. Journal of Alloys and Compounds, 2012, 516, 38-40.	5.5	8
116	Laser-induced periodic structures for light extraction efficiency enhancement of GaN-based light emitting diodes. Optics Express, 2012, 20, 5689.	3.4	36
117	Study of efficiency-droop mechanism in vertical red light-emitting diodes using electrical-to-optical impulse responses. , 2012, , .		0
118	Gallium nitride-based light-emitting diodes with embedded air voids grown on Ar-implanted AlN/sapphire substrate. Applied Physics Letters, 2012, 101, .	3.3	12
119	Vertical InGaN light-emitting diodes with Ag paste as bonding layer. Microelectronics Reliability, 2012, 52, 949-951.	1.7	3
120	Very High-Speed GaN-Based Cyan Light Emitting Diode on Patterned Sapphire Substrate for 1 Gbps Plastic Optical Fiber Communication. , 2012, , .		3
121	The Influence of a Piezoelectric Field on the Dynamic Performance of GaN-Based Green Light-Emitting Diodes With an InGaN Insertion Layer. IEEE Electron Device Letters, 2011, 32, 656-658.	3.9	4
122	Investigation of the Efficiency-Droop Mechanism in Vertical Red Light-Emitting Diodes Using a Dynamic Measurement Technique. IEEE Photonics Technology Letters, 2011, 23, 1585-1587.	2.5	8
123	GaN-Based Light-Emitting Diodes With Air Gap Array and Patterned Sapphire Substrate. IEEE Photonics Technology Letters, 2011, 23, 1207-1209.	2.5	3
124	Effect of Growth Pressure of Undoped GaN Layer on the ESD Characteristics of GaN-Based LEDs Grown on Patterned Sapphire. IEEE Photonics Technology Letters, 2011, 23, 968-970.	2.5	12
125	Characteristics of InGaN/sapphire-based photovoltaic devices with different superlattice absorption layers and buffer layers. , 2011, , .		1
126	Characteristics of InGaN-based concentrator solar cells operating under 150X solar concentration. Optics Express, 2011, 19, A695.	3.4	17

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127	Hydrogen gas generation using n-GaN photoelectrodes with immersed Indium Tin Oxide ohmic contacts. Optics Express, 2011, 19, A1196.	3.4	13
128	Linear photon up-conversion of 450 meV in InGaN/GaN multiple quantum wells via Mn-doped GaN intermediate band photodetection. Optics Express, 2011, 19, A1211.	3.4	9
129	Electroluminescence of ZnO nanocrystal in sputtered ZnO-SiO ₂ nanocomposite light-emitting devices. Optics Express, 2011, 19, 11873.	3.4	9
130	High-performance GaN metal-insulator-semiconductor ultraviolet photodetectors using gallium oxide as gate layer. Optics Express, 2011, 19, 12658.	3.4	39
131	Enhanced output power of GaN-based LEDs with embedded AlGaIn pyramidal shells. Optics Express, 2011, 19, 12719.	3.4	7
132	Enhanced hydrogen gas generation rate by n-GaN photoelectrode with immersed finger-type indium tin oxide ohmic contacts. , 2011, , .		0
133	Investigation of the Carrier Dynamic in GaN-Based Cascade Green Light-Emitting Diodes Using the Very Fast Electrical-Optical Pump-Probe Technique. IEEE Transactions on Electron Devices, 2011, 58, 495-500.	3.0	14
134	Femtosecond ultrasonic spectroscopy using a piezoelectric nanolayer: Hypersound attenuation in vitreous silica films. Applied Physics Letters, 2011, 99, 051913.	3.3	22
135	Improved Power Conversion Efficiency of InGaIn Photovoltaic Devices Grown on Patterned Sapphire Substrates. IEEE Electron Device Letters, 2011, 32, 536-538.	3.9	4
136	Influence of modulated fields on the Landau level properties of graphene. Physical Review B, 2011, 83, .	3.2	12
137	Enhanced Light Output of GaN-Based Light-Emitting Diodes With Embedded Voids Formed on Si-Implanted GaN Layers. IEEE Electron Device Letters, 2011, 32, 1400-1402.	3.9	10
138	Biomimetic surface nanostructure on GaN/In _{0.25} Ga _{0.75} N solar cells for broad angular enhancement. , 2011, , .		0
139	Optical and Electrical Properties of μ -Slice InGaIn/GaN Light Emitting Diodes Shaped by Focused Ion Beam Process. Applied Physics Express, 2011, 4, 032104.	2.4	2
140	Investigation of the efficiency-droop mechanism in a GaN based blue light-emitting diodes using a very-fast electrical-optical pump-probe technique. , 2011, , .		0
141	Femtosecond excitation of confined acoustic modes in 2-D arrayed GaN nanorods. , 2011, , .		0
142	Very-High Temperature (200 $^{\circ}$ C) Operation of GaN-Based Cascade Green Light Emitting Diode for Plastic Optical Fiber Communication. , 2010, , .		0
143	GaN-Based LEDs With AZO:Y Upper Contact. IEEE Transactions on Electron Devices, 2010, 57, 134-139.	3.0	19
144	III-Nitride-Based Light-Emitting Diodes With GaN Micropillars Around Mesa and Patterned Substrate. IEEE Transactions on Electron Devices, 2010, 57, 140-144.	3.0	4

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145	Sub-Bandgap Laser Light-Induced Excess Carrier Transport Between Surface States and Two-Dimensional Electron Gas Channel in AlGaIn/GaN Structure. IEEE Journal of Quantum Electronics, 2010, 46, 112-115.	1.9	4
146	Improved Performance of GaN-Based Blue LEDs With the InGaIn Insertion Layer Between the MQW Active Layer and the n-GaN Cladding Layer. IEEE Journal of Quantum Electronics, 2010, 46, 513-517.	1.9	34
147	GaN-Based Light-Emitting Diodes With Pillar Structures Around the Mesa Region. IEEE Journal of Quantum Electronics, 2010, 46, 1066-1071.	1.9	10
148	AlGaInP/GaP Heterostructures Bonded with Si Substrate to Serve as Solar Cells and Light Emitting Diodes. Journal of the Electrochemical Society, 2010, 157, H452.	2.9	7
149	Improved Hydrogen Gas Generation Rate of n-GaN Photoelectrode with SiO ₂ Protection Layer on the Ohmic Contacts from the Electrolyte. Journal of the Electrochemical Society, 2010, 157, B266.	2.9	11
150	Erbium-Doped All-Fiber Green Up-Conversion Amplified Emission in Silica-Based Fiber System. Japanese Journal of Applied Physics, 2010, 49, 032701.	1.5	0
151	Polarized edge emission from GaN-based light-emitting diodes sandwiched by dielectric/metal hybrid reflectors. Journal of Applied Physics, 2010, 108, 113102.	2.5	2
152	Inverted Al _{0.25} Ga _{0.75} N/GaN ultraviolet p-i-n photodiodes formed on p-GaN template layer grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 013502.	3.3	27
153	Femtosecond laser-ultrasonic investigation of plasmonic fields on the metal/gallium nitride interface. Applied Physics Letters, 2010, 97, .	3.3	12
154	AlGaIn-based ultraviolet photodetector with micropillar structures. Applied Physics Letters, 2010, 96, 102104.	3.3	6
155	GaN-based light emitting diodes with embedded SiO ₂ pillars and air gap array structures. Applied Physics Letters, 2010, 97, .	3.3	27
156	Enhancement of the conversion efficiency of GaN-based photovoltaic devices with AlGaIn/InGaIn absorption layers. Applied Physics Letters, 2010, 97, 021113.	3.3	27
157	Ga-Doped ZnO/GaN Schottky Barrier UV Band-Pass Photodetector with a Low-Temperature-Grown GaN Cap Layer. Japanese Journal of Applied Physics, 2010, 49, 04DF12.	1.5	1
158	Effect of Thermal Annealing on the GaN Metal-Oxide-Semiconductor Capacitors with Gallium Oxide Gate Layer. Journal of the Electrochemical Society, 2010, 157, H1019.	2.9	10
159	InGaIn gallium nitride light-emitting diodes with reflective electrode pads and textured gallium-doped ZnO contact layer. Applied Physics Letters, 2010, 96, 133504.	3.3	21
160	Very-High Temperature (200 °C) and High-Speed Operation of Cascade GaN-Based Green Light-Emitting Diodes With an InGaIn Insertion Layer. IEEE Photonics Technology Letters, 2010, 22, 1033-1035.	2.5	10
161	Characterization of n-GaN with Naturally Textured Surface for Photoelectrochemical Hydrogen Generation. Journal of the Electrochemical Society, 2010, 157, H1106.	2.9	5
162	InGaIn light-emitting diodes with oblique sidewall facets formed by selective growth on SiO ₂ patterned GaN film. Optics Express, 2010, 18, A562.	3.4	6

#	ARTICLE	IF	CITATIONS
163	A Numerical Study of Thermal and Electrical Effects in a Vertical LED Chip. Journal of the Electrochemical Society, 2010, 157, H31.	2.9	24
164	Photodetectors formed by an indium tin oxide/zinc oxide/p-type gallium nitride heterojunction with high ultraviolet-to-visible rejection ratio. Applied Physics Letters, 2009, 94, 013512.	3.3	25
165	The Output Power Enhancements of GaN-Based Blue Light-Emitting Diodes with Highly Reflective Ag/Cr/Au Trilayer Omnidirectional Reflective Electrode Pads. Japanese Journal of Applied Physics, 2009, 48, 102103.	1.5	6
166	GaN-Based LED with Embedded Microlens-like Structure. Journal of the Electrochemical Society, 2009, 156, H976.	2.9	6
167	Characterization of Gallium-Doped Zinc Oxide Contact on n-Type Gallium Nitride Epitaxial Layers. Journal of the Electrochemical Society, 2009, 156, H679.	2.9	2
168	GaN-Based LEDs Output Power Improved by Textured GaN/Sapphire Interface Using <i>In Situ</i> SiH_4 Treatment Process During Epitaxial Growth. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1275-1280.	2.9	13
169	GaN-Based Power Flip-Chip LEDs With Cu Submount. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1287-1291.	2.9	6
170	The Structure of GaN-Based Transverse Junction Blue LED Array for Uniform Distribution of Injected Current/Carriers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1292-1297.	2.9	11
171	Electrical-optical analysis of a GaN/sapphire LED chip by considering the resistivity of the current-spreading layer. Optical Review, 2009, 16, 213-215.	2.0	20
172	High-Brightness InGaN/GaN Power Flip-Chip LEDs. Journal of Lightwave Technology, 2009, 27, 1985-1989.	4.6	12
173	Improvement of the Efficiency of InGaN/GaN Quantum-Well Light-Emitting Diodes Grown With a Pulsed-Trimethylindium Flow Process. IEEE Photonics Technology Letters, 2009, 21, 414-416.	2.5	6
174	Light Output Improvement of Oxide-Textured InGaN-Based Light-Emitting Diodes by Bias-Assisted Photoelectrochemical Oxidation With Imprint Technique. IEEE Photonics Technology Letters, 2009, 21, 718-720.	2.5	5
175	GaN-Based LEDs With Mesh ITO p-Contact and Nanopillars. IEEE Photonics Technology Letters, 2009, 21, 1293-1295.	2.5	2
176	GaN-Based LEDs With GaN μ -Pillars Around Mesa, Patterned Substrate, and Reflector Under Pads. IEEE Photonics Technology Letters, 2009, 21, 1659-1661.	2.5	1
177	Demonstration of GaN-Based Solar Cells With GaN/InGaN Superlattice Absorption Layers. IEEE Electron Device Letters, 2009, 30, 225-227.	3.9	65
178	Array of GaN-based transverse junction blue light emitting diodes with regrown n-type regimes. Proceedings of SPIE, 2009, , .	0.8	0
179	The Bandwidth-Efficiency Product Enhancement of GaN Based Photodiodes by launching a Low-Temperature-Grown Recombination Center in Photo-Absorption Region. , 2009, , .		0
180	Non-lithographic nanopatterning of InGaN/GaN multiple quantum well nanopillars by focused ion beams. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2186-2188.	0.8	2

#	ARTICLE	IF	CITATIONS
181	The CL emission observation of the InGaN/GaN MQWs V shaped pits with different superlattices underlayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1639-1641.	0.8	7
182	Improved Light Extraction Efficiency in AlGaInP Light-Emitting Diodes by Applying a Periodic Texture on the Surface. <i>IEEE Photonics Technology Letters</i> , 2008, 20, 1724-1726.	2.5	11
183	Linear Cascade GaN-Based Green Light-Emitting Diodes With Invariant High-Speed/Power Performance Under High-Temperature Operation. <i>IEEE Photonics Technology Letters</i> , 2008, 20, 1896-1898.	2.5	12
184	Phosphor-Free GaN-Based Transverse Junction White-Light Light-Emitting Diodes With Regrown n-Type Regions. <i>IEEE Photonics Technology Letters</i> , 2008, 20, 449-451.	2.5	13
185	Effect of Thickness of the p-AlGaIn Electron Blocking Layer on the Improvement of ESD Characteristics in GaN-Based LEDs. <i>IEEE Photonics Technology Letters</i> , 2008, 20, 1142-1144.	2.5	38
186	Ga-Doped ZnO Transparent Conductive Oxide Films Applied to GaN-Based Light-Emitting Diodes for Improving Light Extraction Efficiency. <i>IEEE Journal of Quantum Electronics</i> , 2008, 44, 1211-1218.	1.9	32
187	High-Speed GaN-Based Green Light-Emitting Diodes With Partially n-Doped Active Layers and Current-Confined Apertures. <i>IEEE Electron Device Letters</i> , 2008, 29, 158-160.	3.9	60
188	Alternating current bias-assisted photoenhanced oxidation of n-GaN in dionized water. <i>Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on</i> , 2008, , .	0.0	1
189	Focused Ion Beam Milled InGaIn/GaN Multiple Quantum Well Nanopillars. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 3130-3133.	1.5	3
190	Low Operation Voltage of Nitride-Based LEDs with Al-Doped ZnO Transparent Contact Layer. <i>Electrochemical and Solid-State Letters</i> , 2008, 11, H269.	2.2	24
191	Enhancement in output power of blue gallium nitride-based light-emitting diodes with omnidirectional metal reflector under electrode pads. <i>Applied Physics Letters</i> , 2008, 93, 103507.	3.3	43
192	Effect of the Electrode Pattern on Current Spreading and Driving Voltage in a GaN ⁺ Sapphire LED Chip. <i>Journal of the Electrochemical Society</i> , 2008, 155, H836.	2.9	30
193	Four-Wavelengths-Mixed White Light Emitting Diodes with Dual-Wavelength-Pumped Green and Red Phosphors. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 6317-6319.	1.5	0
194	High-speed and high-power GaN-based cascade green Light-Emitting-Diode arrays for in-car data communication. , 2008, , .		0
195	Ultraviolet bandpass Al _{0.17} Ga _{0.83} N ⁺ GaN heterojunction phototransistors with high optical gain and high rejection ratio. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	26
196	Ultraviolet band-pass photodetectors formed by Ga-doped ZnO contacts to n-GaN. <i>Applied Physics Letters</i> , 2008, 92, 113512.	3.3	17
197	Enhanced efficiency of GaN-based light-emitting diodes with periodic textured Ga-doped ZnO transparent contact layer. <i>Applied Physics Letters</i> , 2007, 90, 263511.	3.3	83
198	Temperature-dependent study of n-ZnO ⁺ p-GaN diodes. <i>Applied Physics Letters</i> , 2007, 90, 132111.	3.3	17

#	ARTICLE	IF	CITATIONS
199	Hole escape processes detrimental to photoluminescence efficiency in a blue InGaN multiple-quantum-well diode under reverse bias conditions. Applied Physics Letters, 2007, 90, 161109.	3.3	2
200	Largely variable electroluminescence efficiency with current and temperature in a blue (In, Ga)N multiple-quantum-well diode. Applied Physics Letters, 2007, 91, .	3.3	8
201	Nonalloyed Cr ²⁺ -Au-based Ohmic contacts to n-GaN. Applied Physics Letters, 2007, 91, .	3.3	74
202	Effect of Thermal Annealing on Ga-Doped ZnO Films Prepared by Magnetron Sputtering. Journal of the Electrochemical Society, 2007, 154, H521.	2.9	61
203	Variations of Channel Conductance in AlGaIn/GaN Structure with Sub-Bandgap Laser Light and Above-Bandgap Illuminations. Japanese Journal of Applied Physics, 2007, 46, 3382-3384.	1.5	6
204	Crack-Free High-Brightness InGaIn ⁺ -GaN LEDs on Si(111) with Initial AlGaIn Buffer and Two LT-Al Interlayers. Journal of the Electrochemical Society, 2007, 154, H191.	2.9	9
205	GaN-Based Ultraviolet p-i-n Photodiodes with Buried p-Layer Structure Grown by MOVPE. Journal of the Electrochemical Society, 2007, 154, H182.	2.9	5
206	Phosphor-Free GaN-Based Cascade Transverse Junction Light Emitting Diode Arrays for the High-Power Generation of White-Light. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
207	Nitride-based light emitting diodes with indium tin oxide electrode patterned by imprint lithography. Applied Physics Letters, 2007, 91, 013504.	3.3	67
208	Improved Reliability and ESD Characteristics of Flip-Chip GaN-Based LEDs With Internal Inverse-Parallel Protection Diodes. IEEE Electron Device Letters, 2007, 28, 346-349.	3.9	37
209	Linear Cascade Arrays of GaN-Based Green Light-Emitting Diodes for High-Speed and High-Power Performance. IEEE Photonics Technology Letters, 2007, 19, 1368-1370.	2.5	15
210	Effects of leakage current and Schottky-like ohmic contact on the characterization of Al _{0.17} Ga _{0.83} N/GaN HBTs. Solid-State Electronics, 2007, 51, 1073-1078.	1.4	5
211	AlGaIn ultraviolet metal-semiconductor-metal photodetectors grown on Si substrates. Sensors and Actuators A: Physical, 2007, 135, 502-506.	4.1	19
212	GaN-based p-i-n sensors with ITO contacts. IEEE Sensors Journal, 2006, 6, 406-411.	4.7	29
213	Flip-Chip p(GaN)-i(GaN)-n(AlGaIn) Narrowband UUV-A Photosensors. IEEE Sensors Journal, 2006, 6, 964-969.	4.7	6
214	Nitride-based photodiode at 510-nm wavelength for plastic optical fiber communication. IEEE Photonics Technology Letters, 2006, 18, 283-285.	2.5	7
215	Enhanced light output of GaN-based power LEDs with transparent Al-doped ZnO current spreading layer. IEEE Photonics Technology Letters, 2006, 18, 274-276.	2.5	72
216	High efficiency and improved ESD characteristics of GaN-based LEDs with naturally textured surface grown by MOCVD. IEEE Photonics Technology Letters, 2006, 18, 1213-1215.	2.5	66

#	ARTICLE	IF	CITATIONS
217	The improvement in modulation speed of GaN-based Green light-emitting diode (LED) by use of n-type barrier doping for plastic optical fiber (POF) communication. IEEE Photonics Technology Letters, 2006, 18, 1636-1638.	2.5	32
218	Phosphor-Free GaN-Based Transverse Junction Light Emitting Diodes for the Generation of White Light. IEEE Photonics Technology Letters, 2006, 18, 2593-2595.	2.5	19
219	External Field Effects on Photoluminescence Properties of Blue InGaN Quantum-Well Diodes. , 2006, , .		0
220	Highly Reliable Nitride-Based LEDs With Internal ESD Protection Diodes. IEEE Transactions on Device and Materials Reliability, 2006, 6, 442-447.	2.0	13
221	Planar Ultraviolet Photodetectors Formed by Si Implantation into p-GaN. Journal of the Electrochemical Society, 2006, 153, G799.	2.9	3
222	Applications of transparent Al-doped ZnO contact on GaN-based power LED. , 2006, , .		1
223	Emission Mechanism of Mixed-Color InGaN/GaN Multi-Quantum-Well Light-Emitting Diodes. Japanese Journal of Applied Physics, 2006, 45, 2463-2466.	1.5	35
224	Nitride-Based Flip-Chip p-i-n Photodiodes. IEEE Transactions on Advanced Packaging, 2006, 29, 483-487.	1.6	3
225	Electroluminescence efficiency of blue InGaN/GaN quantum-well diodes with and without an n-InGaN electron reservoir layer. Journal of Applied Physics, 2006, 100, 113105.	2.5	44
226	Ultraviolet band-pass Schottky barrier photodetectors formed by Al-doped ZnO contacts to n-GaN. Applied Physics Letters, 2006, 88, 043506.	3.3	30
227	InGaN light-emitting diodes with naturally formed truncated micropylramids on top surface. Applied Physics Letters, 2006, 88, 113505.	3.3	43
228	Improved performance of planar GaN-based p-i-n photodetectors with Mg-implanted isolation ring. Applied Physics Letters, 2006, 89, 183509.	3.3	13
229	Low Schottky barrier to etched p-GaN using regrown AlInGaN and InGaN contact layer. Journal of Applied Physics, 2006, 99, 026106.	2.5	2
230	Schottky barrier heights of metal contacts to n-type gallium nitride with low-temperature-grown cap layer. Applied Physics Letters, 2006, 88, 032103.	3.3	45
231	Planar GaN p-i-n photodiodes with n ⁺ -conductive channel formed by Si implantation. Applied Physics Letters, 2006, 88, 203508.	3.3	8
232	Modulation-speed enhancement of a GaN based green light-emitting-diode (LED) by use of n-type barrier doping for plastic optical fiber (POF) communication. , 2006, , .		0
233	AlGaIn/GaN Schottky-barrier UV-B bandpass photodetectors with ITO contacts and LT-GaN cap layers. Semiconductor Science and Technology, 2006, 21, 1064-1068.	2.0	13
234	Effects of Thermal Annealing on Al-Doped ZnO Films Deposited on p-Type Gallium Nitride. Journal of the Electrochemical Society, 2006, 153, G296.	2.9	25

#	ARTICLE	IF	CITATIONS
235	AlGaIn-GaN Schottky-barrier photodetectors with LT GaN cap layers. Journal of Crystal Growth, 2005, 283, 68-71.	1.5	10
236	ICP etching of sapphire substrates. Optical Materials, 2005, 27, 1171-1174.	3.6	58
237	Fabrication and Characterization of In _{0.25} Ga _{0.75} N/GaN Multiple Quantum Wells Embedded in Nanorods. Japanese Journal of Applied Physics, 2005, 44, 7723-7725.	1.5	3
238	Photoluminescence from In _{0.3} Ga _{0.7} N/GaN multiple-quantum-well nanorods. Nanotechnology, 2005, 16, 448-450.	2.6	6
239	Effect of Cl ₂ -Ar dry etching on p-GaN with Ni-Au metallization characterization. Applied Physics Letters, 2005, 87, 252107.	3.3	16
240	Rectifying characteristics of WSi _{0.8} -GaN Schottky barrier diodes with a GaN cap layer grown at low temperature. Journal of Applied Physics, 2005, 98, 036106.	2.5	2
241	Aluminum gallium nitride ultraviolet photodiodes with buried p-layer structure. Applied Physics Letters, 2005, 87, 043501.	3.3	5
242	Effects of Thermal Annealing on Si-Implanted GaN Films Grown at Low Temperature by Metallorganic Vapor Phase. Journal of the Electrochemical Society, 2005, 152, G813.	2.9	3
243	Effect of low-temperature-grown GaN cap layer on reduced leakage current of GaN Schottky diodes. Applied Physics Letters, 2005, 86, 052103.	3.3	53
244	Comparison of low-temperature GaN, SiO ₂ , and SiN _x as gate insulators on AlGaIn-GaN heterostructure field-effect transistors. Journal of Applied Physics, 2005, 98, 064506.	2.5	20
245	Enhancement in light output of InGaIn-based microhole array light-emitting diodes. IEEE Photonics Technology Letters, 2005, 17, 1163-1165.	2.5	50
246	Enhanced output power in GaN-based LEDs with naturally textured surface grown by MOCVD. IEEE Electron Device Letters, 2005, 26, 464-466.	3.9	53
247	Gratings in GaN Membranes. Japanese Journal of Applied Physics, 2004, 43, 5854-5856.	1.5	4
248	Si diffusion in p-GaN. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1727.	1.6	14
249	Effect of GaN cap layer grown at a low temperature on electrical characteristics of Al _{0.25} Ga _{0.75} N-GaN heterojunction field-effect transistors. Applied Physics Letters, 2004, 85, 1430-1432.	3.3	9
250	Nitride-Based LEDs With Modulation-Doped Al _{0.12} Ga _{0.88} N-GaN Superlattice Structures. IEEE Transactions on Electron Devices, 2004, 51, 1743-1746.	3.0	38
251	Nitride-based near-ultraviolet LEDs with an ITO transparent contact. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 106, 69-72.	3.5	52
252	Lateral epitaxial patterned sapphire InGaIn/GaN MQW LEDs. Journal of Crystal Growth, 2004, 261, 466-470.	1.5	67

#	ARTICLE	IF	CITATIONS
253	Reduction of Dark Current in AlGaIn/GaN Schottky-Barrier Photodetectors With a Low-Temperature-Grown GaN Cap Layer. IEEE Electron Device Letters, 2004, 25, 593-595.	3.9	37
254	Nitride-Based LEDs With an SPS Tunneling Contact Layer and an ITO Transparent Contact. IEEE Photonics Technology Letters, 2004, 16, 1002-1004.	2.5	70
255	Nitride-Based LEDs With 800Å-Grown p-AlInGa/GaN Double-Cap Layers. IEEE Photonics Technology Letters, 2004, 16, 1447-1449.	2.5	95
256	Fabrication and emission characteristic of InGaIn/GaN multiple quantum wells nanorods. , 2004, , IWA20.		1
257	Electrical-efficiency analysis of GaN-based light-emitting diodes with interdigitated-mesa geometry. Journal of Electronic Materials, 2003, 32, 312-315.	2.2	0
258	Gallium Nitride Diffractive Microlenses Using in Ultraviolet Micro-Optics System. Optical Review, 2003, 10, 287-289.	2.0	3
259	Si and Zn co-doped InGaIn-GaN white light-emitting diodes. IEEE Transactions on Electron Devices, 2003, 50, 519-521.	3.0	31
260	Nitride-based light emitting diodes with Si-doped In _{0.23} Ga _{0.77} N/GaN short period superlattice tunneling contact layer. IEEE Transactions on Electron Devices, 2003, 50, 535-537.	3.0	8
261	Nitride-based green light-emitting diodes with high temperature GaN barrier layers. IEEE Transactions on Electron Devices, 2003, 50, 1766-1770.	3.0	23
262	High brightness ingan green leds with an ito on n ⁺⁺ -sps upper contact. IEEE Transactions on Electron Devices, 2003, 50, 2208-2212.	3.0	28
263	GaN diffractive microlenses fabricated with gray-level mask. Optics Communications, 2003, 215, 75-78.	2.1	11
264	Visible-blind GaIn photodiodes with an Al _{0.12} Ga _{0.88} N/GaN superlattice structure. Solid-State Electronics, 2003, 47, 873-878.	1.4	19
265	Nitride-based blue LEDs with GaN/SiN double buffer layers. Solid-State Electronics, 2003, 47, 2019-2022.	1.4	21
266	In _{0.23} Ga _{0.77} N/GaN MQW LEDs with a low temperature GaN cap layer. Solid-State Electronics, 2003, 47, 2027-2030.	1.4	58
267	MOCVD growth of InGaIn/GaN blue light emitting diodes on patterned sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2253-2256.	0.8	4
268	High brightness InGaIn/GaN LEDs with indium-tin-oxide as p-electrode. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2227-2231.	0.8	5
269	White-light emission from near UV InGaIn-GaN LED chip precoated with blue/green/red phosphors. IEEE Photonics Technology Letters, 2003, 15, 18-20.	2.5	607
270	Improvement of near-ultraviolet InGaIn-GaN light-emitting diodes through higher pressure grown underlying GaN layers. IEEE Photonics Technology Letters, 2003, 15, 1050-1052.	2.5	7

#	ARTICLE	IF	CITATIONS
271	Improvement of near-ultraviolet InGaN-GaN light-emitting diodes with an AlGaIn electron-blocking layer grown at low temperature. IEEE Photonics Technology Letters, 2003, 15, 1342-1344.	2.5	37
272	Improved ESD protection by combining InGaN-GaN MQW LEDs with GaN Schottky diodes. IEEE Electron Device Letters, 2003, 24, 129-131.	3.9	63
273	Improvement of InGaN/GaN laser diodes by using a Si-doped In/sub 0.23/Ga/sub 0.77/N/GaN short-period superlattice tunneling contact layer. IEEE Electron Device Letters, 2003, 24, 206-208.	3.9	14
274	Characterization of GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. Journal of Applied Physics, 2003, 94, 1753-1757.	2.5	37
275	Deep level defect in Si-implanted GaN ϵ S ϵ n+p junction. Applied Physics Letters, 2003, 82, 3671-3673.	3.3	20
276	GaN metal-semiconductor-metal photodetectors with low-temperature-GaN cap layers and ITO metal contacts. IEEE Electron Device Letters, 2003, 24, 212-214.	3.9	93
277	GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. Applied Physics Letters, 2003, 82, 2913-2915.	3.3	46
278	Carrier dynamics in nitride-based light-emitting p-n junction diodes with two active regions emitting at different wavelengths. Journal of Applied Physics, 2003, 94, 2167-2172.	2.5	57
279	Experimental study of perpendicular transport in weakly coupled Al ϵ Ga1 ϵ xN/GaN superlattices. Applied Physics Letters, 2003, 83, 4975-4977.	3.3	20
280	n-UV+Blue/Green/Red White Light Emitting Diode Lamps. Japanese Journal of Applied Physics, 2003, 42, 2284-2287.	1.5	90
281	GaN light-emitting diodes with omnidirectional reflectors. , 2003, 4996, 139.		11
282	Piezoelectric effect on Al ϵ .35 ϵ 1 ϵ 1 ϵ Ga ϵ .65N/GaN heterostructures. Applied Physics Letters, 2002, 80, 2684-2686.	3.3	10
283	Planar GaN n+ ϵ p photodetectors formed by Si implantation into p-GaN. Applied Physics Letters, 2002, 81, 4263-4265.	3.3	42
284	High brightness green light emitting diodes with charge asymmetric resonance tunneling structure. IEEE Electron Device Letters, 2002, 23, 130-132.	3.9	52
285	Ohmic contacts to p-type GaN mediated by polarization fields in thin In ϵ Ga1 ϵ xN capping layers. Applied Physics Letters, 2002, 80, 986-988.	3.3	65
286	n+-GaN formed by Si implantation intop-GaN. Journal of Applied Physics, 2002, 91, 1845-1848.	2.5	52
287	White-light emission from InGaIn-GaN multiquantum-well light-emitting diodes with Si and Zn codoped active well layer. IEEE Photonics Technology Letters, 2002, 14, 450-452.	2.5	86
288	Nitride-based cascade near white light-emitting diodes. IEEE Photonics Technology Letters, 2002, 14, 908-910.	2.5	77

#	ARTICLE	IF	CITATIONS
289	InGaN/GaN light emitting diodes activated in O/sub 2/ ambient. IEEE Electron Device Letters, 2002, 23, 240-242.	3.9	60
290	The doping process and dopant characteristics of GaN. Journal of Physics Condensed Matter, 2002, 14, R657-R702.	1.8	93
291	GaN metal-semiconductor-metal ultraviolet sensors with various contact electrodes. IEEE Sensors Journal, 2002, 2, 366-371.	4.7	99
292	Influence of Si-doping on the characteristics of InGaN-GaN multiple quantum-well blue light emitting diodes. IEEE Journal of Quantum Electronics, 2002, 38, 446-450.	1.9	147
293	400-nm InGaN-GaN and InGaN-AlGaIn multiquantum well light-emitting diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 744-748.	2.9	213
294	Characterization of Si implants in p-type GaN. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 767-772.	2.9	34
295	High-efficiency InGaN-GaN MQW green light-emitting diodes with CART and DBR structures. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 284-288.	2.9	59
296	InGaN/GaN tunnel-injection blue light-emitting diodes. IEEE Transactions on Electron Devices, 2002, 49, 1093-1095.	3.0	52
297	Novel type of ohmic contacts to p-doped GaN using polarization fields in thin In _x Ga _{1-x} N capping layers. Journal of Electronic Materials, 2002, 31, 416-420.	2.2	7
298	Dependence of optical gain on direction of optically pumped cavity on (0001)-plane for InGaN/GaN multiple quantum well structure. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 28-30.	3.5	2
299	Observation of dislocation etch pits in epitaxial lateral overgrowth GaN by wet etching. Solid-State Electronics, 2002, 46, 555-558.	1.4	22
300	GaN p-n junction diode formed by Si ion implantation into p-GaN. Solid-State Electronics, 2002, 46, 2179-2183.	1.4	20
301	InGaN-AlInGaIn multiquantum-well LEDs. IEEE Photonics Technology Letters, 2001, 13, 559-561.	2.5	100
302	GaN metal-semiconductor-metal ultraviolet photodetectors with transparent indium-tin-oxide Schottky contacts. IEEE Photonics Technology Letters, 2001, 13, 848-850.	2.5	144
303	Enhanced output power in an InGaN-GaN multiquantum-well light-emitting diode with an InGaIn current-spreading layer. IEEE Photonics Technology Letters, 2001, 13, 1164-1166.	2.5	39
304	Low-operation voltage of InGaN/GaN light-emitting diodes by using a Mg-doped Al _{0.15} Ga _{0.85} N/GaN superlattice. IEEE Electron Device Letters, 2001, 22, 160-162.	3.9	44
305	Crystal orientation dependence of optical gain in InGaN/GaN multiple-quantum-well structures. Applied Physics Letters, 2001, 79, 1477-1479.	3.3	7
306	Low-operation voltage of InGaN-GaN light-emitting diodes with Si-doped In _{0.3} Ga _{0.7} N/GaN short-period superlattice tunneling contact layer. IEEE Electron Device Letters, 2001, 22, 460-462.	3.9	125

#	ARTICLE	IF	CITATIONS
307	Characterization of the properties of Mg-doped Al _{0.15} Ga _{0.85} N/GaN superlattices. Solid-State Electronics, 2001, 45, 1665-1671.	1.4	3
308	Characterization of p-type In _x Ga _{1-x} N grown by metalorganic chemical vapor deposition. Solid-State Electronics, 2001, 45, 427-430.	1.4	12
309	Low-resistance Ni/Au ohmic contact to Mg-doped Al _{0.15} Ga _{0.85} N/GaN superlattices. Solid-State Electronics, 2001, 45, 717-720.	1.4	16
310	Polymer PBT/n-GaN metal-insulator-semiconductor structure. Applied Physics Letters, 2001, 79, 4589-4591.	3.3	18
311	Luminescence of an InGaN/GaN multiple quantum well light-emitting diode. Solid-State Electronics, 2000, 44, 1055-1058.	1.4	32
312	Investigation of the mechanism for Ti/Al ohmic contact on etched n-GaN surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 729.	1.6	39
313	Indium tin oxide ohmic contact to highly doped n-GaN. Solid-State Electronics, 1999, 43, 2081-2084.	1.4	35
314	Electrical derivative characteristics of ion-implanted AlGaInP/GaInP multi-quantum well lasers. Solid-State Electronics, 1998, 42, 1867-1869.	1.4	9
315	Effects of thermal annealing on the indium tin oxide Schottky contacts of n-GaN. Applied Physics Letters, 1998, 72, 3317-3319.	3.3	150
316	AlGaInP/GaP Light-Emitting Diodes Fabricated by Wafer Direct Bonding Technology. Japanese Journal of Applied Physics, 1996, 35, 4199-4202.	1.5	11
317	UV, blue, green, yellow-green and white LEDs fabricated by III-N semiconductors. , 0, , .		1
318	GaN diffractive microlenses for UV micro-optics system. , 0, , .		1
319	400nm InGaN/GaN and InGaN/AlGaIn multiquantum well light-emitting diodes. , 0, , .		3
320	Improved esd reliability by using a modulation doped Al/sub 0.12/Ga/sub 0.88/N/GaN superlattice in nitride-based led. , 0, , .		1
321	Optical properties of InGaN/GaN nanorods fabricated by inductively coupled plasma etching. , 0, , .		0